TOSHIBA MOS MEMORY PRODUCTS

TMM2464AP/AF 8,192 WORD × 8 BIT
ONE TIME PROGRAMMABLE READ ONLY MEMORY
N CHANNEL SILICON STACKED GATE MOS

TMM2464AP/AF

DESCRIPTION

The TMM2464AP/AF is a 8,192 word × 8 bit one time programmable read only memory, and molded in a 28 pin plastic DIP.

The TMM2464AP/AF's access time is 200ns, and has low power standby mode which reduces the power dissipation without increasing access time.

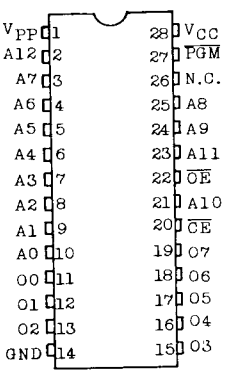
The electrical characteristics and programming method are the same as U. V. EPROM TMM-2764AD's.

Once programed, the TMM2464AP/AF can not be erased because of using plastic DIP without transparent window.

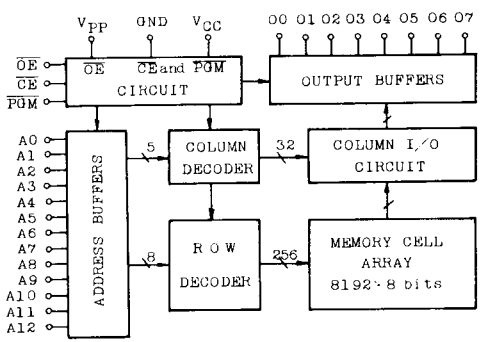
FEATURES

- Single 5 volt power supply
- Fast access time: 200ns (Max.)
- Power dissipation : 100mA(active current) Max.
  : 30mA(standby current) Max.
- Low power standby mode : $\overline{CE}$
- Output buffer control : $\overline{OE}$
- Full static operation
- High speed programming mode
- Three state outputs
- Inputs and outputs TTL compatible
- Compatible with TMM2764AD and ROM TMM2365P, TC5365P.
- 28 PIN standard plastic package: TMM2464AP
- 28 PIN flat package : TMM2464AF

PIN CONNECTION (TOP VIEW)



BLOCK DIAGRAM



PIN NAMES

$A_0 \sim A_{12}$	Address Inputs
$O_0 \sim O_7$	Outputs (Inputs)
$\overline{CE}$	Chip Enable Input
$\overline{OE}$	Output Enable Input
$\overline{PGM}$	Program Control Input
N.C.	No Connection
V_{PP}	Program Supply Voltage
V_{CC}	V_{CC} Supply Voltage (+5V)
GND	Ground

MODE SELECTION

MODE \ PIN	$\overline{PGM}$ (27)	$\overline{CE}$ (20)	$\overline{OE}$ (22)	V_{PP} (1)	V_{CC} (28)	$O_0 \sim O_7$ (11~13, 15~19)	POWER
Read	H	L	L	5V	5V	Data Out	Active
Output Deselect	*	*	H			High Impedance	
Standby	*	H	*			High Impedance	Standby
Program	L	L	*	12.5V	6V	Data In	Active
Program Inhibit	*	H	*			High Impedance	
	H	L	H			High Impedance	
Program Verify	H	L	L			Data Out	

* H or L

MAXIMUM RATINGS

SYMBOL	ITEM	RATING	UNIT
V_{CC}	V_{CC} Power Supply Voltage	−0.6~7.0	V
V_{PP}	Program Supply Voltage	−0.6~14.0	V
V_{IN}	Input Voltage	−0.6~7.0	V
V_{OUT}	Output Voltage	−0.6~7.0	V
P_D	Power Dissipation	1.5	W
T_{SOLDER}	Soldering Temperature · Time	260 · 10	°C·sec
T_{STRG}	Storage Temperature	−55~150	°C
T_{OPR}	Operating Temperature	0~70	°C

READ OPERATION

D. C. RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	MIN.	TYP.	MAX.	UNIT
V_{IH}	Input High Voltage	2.2	−	V_{CC}+1.0	V
V_{IL}	Input Low Voltage	−0.3	−	0.8	
V_{CC}	V_{CC} Power Supply Voltage	4.75	5.00	5.25	
V_{PP}	V_{PP} Power Supply Voltage	2.2	V_{CC}	V_{CC}+0.6	

D. C. and OPERATING CHARACTERISTICS

($Ta=0\sim70°C$, $V_{CC}=5V\pm5\%$, Unless otherwise noted)

SYMBOL	PARAMETER	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
I_{LI}	Input Current	$V_{IN}=0\sim V_{CC}$	−	−	±10	μA
I_{CC1}	Supply Current (Standby)	$\overline{CE}=V_{IH}$	−	−	30	mA
I_{CC2}	Supply Current (Active)	$\overline{CE}=V_{IL}$	−	−	100	mA
V_{OH}	Output High Voltage	$I_{OH}=-400\mu A$	2.4	−	−	V
V_{OL}	Output Low Voltage	$I_{OL}=2.1mA$	−	−	0.4	V
I_{PP1}	V_{PP} Current	$V_{PP}=0\sim V_{CC}+0.6V$	−	−	±10	μA
I_{LO}	Output Leakage Current	$V_{OUT}=0.4V\sim V_{CC}$	−	−	±10	μA

A. C. CHARACTERISTICS (Ta = 0 ~ 70 C, V... = 5V ± 5%, V... = 2.0V ~ V... + 0.6V, Unless otherwise noted)

SYMBOL	PARAMETER	MIN.	MAX.	UNIT
t_{ACC}	Address Access Time	—	200	ns
t_{CE}	$\overline{CE}$ to Output Valid	—	200	ns
t_{OE}	$\overline{OE}$ to Output Valid	—	70	ns
t_{PGM}	$\overline{PGM}$ to Output Valid	—	70	ns
t_{DF1}	$\overline{CE}$ to Output in High-Z	0	60	ns
t_{DF2}	$\overline{OE}$ to Output in High-Z	0	60	ns
t_{DF3}	$\overline{PGM}$ to Output in High-Z	0	60	ns
t_{OH}	Output Data Hold Time	0	—	ns

A. C. TEST CONDITIONS

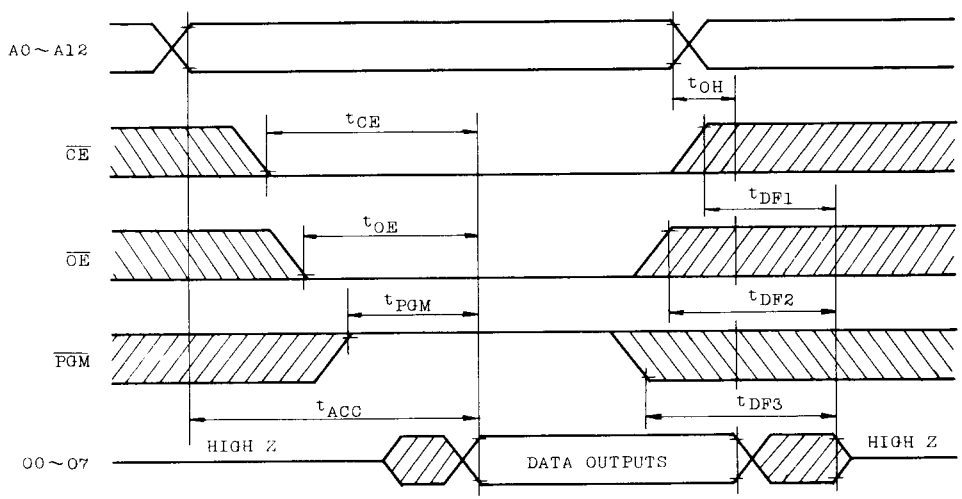
- Output Load : 1 TTL Gate and C_L = 100pF
- Input Pulse Rise and Fall Times : 10ns Max.
- Input Pulse Levels : 0.45V to 2.4V
- Timing Measurement Reference Level : Inputs 0.8V and 2.0V, Outputs 0.8V and 2.0V

CAPACITANCE * (Ta = 25 C, f = 1MHz)

SYMBOL	PARAMETER	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
C_{IN}	Input Capacitance	V_{IN} = 0V	—	4	6	pF
C_{OUT}	Output Capacitance	V_{OUT} = 0V	—	8	12	pF

* This parameter is periodically sampled and is not 100% tested.

TIMING WAVEFORMS



HIGH SPEED PROGRAM OPERATION

D. C. RECOMMENDED OPERATING CONDITIONS

SYMBOL	PARAMETER	MIN.	TYP.	MAX.	UNIT
V_{IH}	Input High Voltage	2.0		$V_{CC}+1.0$	V
V_{IL}	Input Low Voltage	-0.3		0.8	V
V_{CC}	V_{CC} Power Supply Voltage	5.75	6.0	6.25	V
V_{PP}	V_{PP} Power Supply Voltage	12.0	12.5	13.0	V

D. C. and OPERATING CHARACTERISTICS

($Ta=25\pm5°C$, $V_{CC}=6V\pm0.25V$, $V_{PP}=12.5V\pm0.5V$)

SYMBOL	PARAMETER	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
I_{LI}	Input Current	$V_{IN}=0\sim V_{CC}$	—	—	±10	μA
V_{OH}	Output High Voltage	$I_{OH}=-400\mu A$	2.4	—	—	V
V_{OL}	Output Low Voltage	$I_{OL}=2.1mA$	—	—	0.4	V
I_{CC}	V_{CC} Supply Current	—	—	—	100	mA
I_{PP2}	V_{PP} Supply Current	$V_{PP}=13.0V$	—	—	50	mA

A. C. PROGRAMMING CHARACTERISTICS

($Ta=25\pm5°C$, $V_{CC}=6V+0.25V$, $V_{PP}=12.5V\pm0.5V$)

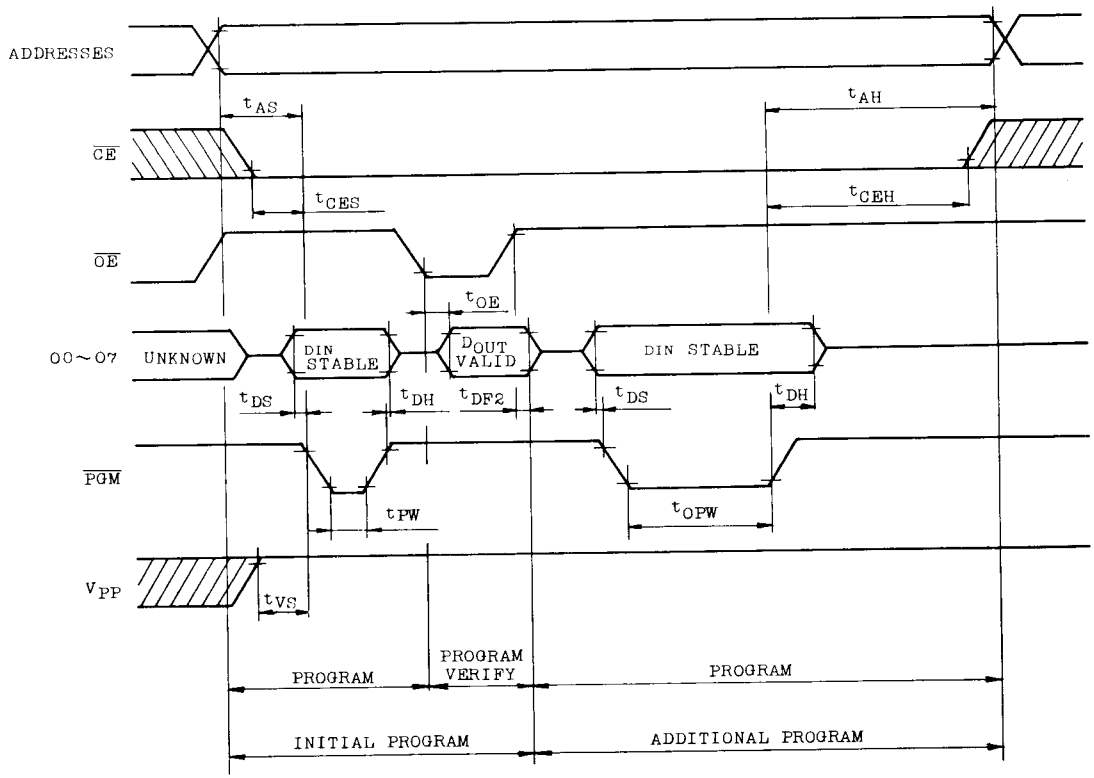
SYMBOL	PARAMETER	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
t_{AS}	Address Setup Time	—	2	—	—	μs
t_{AH}	Address Hold Time	—	2	—	—	μs
t_{CES}	$\overline{CE}$ Setup Time	—	2	—	—	μs
t_{CEH}	$\overline{CE}$ Hold Time	—	2	—	—	μs
t_{DS}	Data Setup Time	—	2	—	—	μs
t_{DH}	Data Hold Time	—	2	—	—	μs
t_{VS}	V_{PP} Setup Time	—	2	—	—	μs
t_{PW}	Program Pulse Width	—	0.95	1.0	1.05	ms
t_{OPW}	Additional Program Pulse Width	Note 1	2.85	3.0	78.75	ms
t_{OE}	$\overline{OE}$ to Output Valid	—	—	—	100	ns
t_{DF2}	$\overline{OE}$ to Output in High-Z	$\overline{CE}=V_{IL}$	—	—	90	ns

A. C. TEST CONDITIONS

- Output Load : 1 TTL Gate and C_L (100pF)
- Input Pulse Rise and Fall Times : 10ns Max.
- Input Pulse Levels : 0.45V to 2.4V
- Timing Measurement Reference Level : Input 0.8V and 2.0V, Output 0.8V and 2.0V

Note : 1. t_{OPW} depend on the program pulse width which is reguired in the initial program.

TIMING WAVEFORMS (HIGH SPEED PROGRAM)



Note : 1. V_{CC} must be applied simultaneously or before V_{PP} and cut off simultaneously or after V_{PP}.
2. Removing the device from socket and setting the device in socket with V_{PP} = 12.5V may cause permanent damage to the device.
3. The V_{PP} supply voltage is permitted up to 14V for program operation, so the voltage over 14V should not be applied to the V_{PP} terminal.
When the switching pulse voltage is applied to the V_{PP} terminal, the overshoot voltage of its pulse should not be exceeded 14V.

OPERATION INFORMATION

The TMM2464AP/AF's six operation modes are listed in the following table. Mode selection can be achieved by applying TTL level signal to all inputs. In the read operation mode, a single 5V power supply is required and the levels required for all inputs are TTL.

MODE \ PIN NAMES(NUMBER)		$\overline{PGM}$ (27)	$\overline{CE}$ (20)	$\overline{OE}$ (22)	V_{PP} (1)	V_{CC} (28)	$O_0 \sim O_7$ (11~13, 15~19)	POWER
Read Operation (Ta=0~70°C)	Read	H	L	L	5V	5V	Data Out	Active
	Output Deselect	*	*	H			High Impedance	Active
	Standby	*	H	*			High Impedance	Standby
Program Operation (Ta=25±5°C)	Program	L	L	*	12.5V	6V	Data In	Active
	Program Inhibit	*	H	*			High Impedance	Active
		H	L	H			High Impedance	Active
	Program Verify	H	L	L			Data Out	Active

Note : H ; V_{IH}, L ; V_{IL}, * ; V_{IH} or V_{IL}

READ MODE

The TMM2464AP/AF has three control functions. The chip enable ($\overline{CE}$) controls the operation power and should be used for device selection.

The output enable ($\overline{OE}$) and the program control ($\overline{PGM}$) control the output buffers, independent of device selection.

Assuming that $\overline{CE}=\overline{OE}=V_{IL}$ and $\overline{PGM}=V_{IH}$, the output data is valid at the outpus after address access time from stabilizing of all addresses.

The $\overline{CE}$ to output valid (t_{CE}) is equal to the address access time (t_{ACC}).

Assuming that $\overline{CE}=V_{IL}$, $\overline{PGM}=V_{IH}$ and all addresses are valid, the output data is valid at the outputs after t_{OE} from the falling edge of $\overline{OE}$.

And assuming that $\overline{CE}=\overline{OE}=V_{IL}$ and all addresses are valid, the output data is valid at the outputs after t_{PGM} from the rising edge of $\overline{PGM}$.

OUTPUT DESELECT MODE

Assuming that $\overline{CE}=V_{IH}$ or $\overline{OE}=V_{IH}$, the outputs will be in a high impedance state. So two or more TMM2464AP/AF can be connected together on a common bus line.

When $\overline{CE}$ is decoded for device selection, all deselected devices are in low power standby mode.

STANDBY MODE

The TMM2464AP/AF has a low power standby mode controlled by the $\overline{CE}$ signal. By applying a TTL high level to the $\overline{CE}$ input, the TMM2464AP/AF is placed in the standby mode which reduce the operating current from 100mA to 30mA, and then the outputs are in a high impedance state, independent of the $\overline{OE}$ and the $\overline{PGM}$ inputs.

PROGRAM VERIFY MODE

The verify mode is to check that the desired data is correctly programmed on the programmed bits.

The verify is accomplished with $\overline{OE}$ and $\overline{CE}$ at V_{IL} and $\overline{PGM}$ at V_{IH}.

PROGRAM INHIBIT MODE

Under the condition that the program voltage (+12.5V) is applied to V_{PP} terminal, a high level $\overline{CE}$ or $\overline{PGM}$ input inhibits the TMM2464AP/AF from being programmed. Programming of two or more TMM2464AP/AF in parallel with different data is easily accomplished. That is, all inputs except for $\overline{CE}$ or $\overline{PGM}$ may be commonly connected, and a TTL low level program pulse is applied to the $\overline{CE}$ and $\overline{PGM}$ of the desired device only and TTL high level signal is applied to the other devices.

HIGH SPEED PROGRAMMING MODE

The device is set up in the high speed programming mode when the programming voltage (+12.5V) is applied to the V_{PP} terminal with $V_{CC}=6V$ and $\overline{PGM}=V_{IH}$. The programming is achieved by applying a single TTL low level 1ms pulse the $\overline{PGM}$ input after addresses and data are stable. Then the programmed data is verified by using Program Verify Mode.

If the programmed data is not correct, another program pulse of 1ms is applied and then programmed data is verified. This should be repeated until the program operates correctly (max. 25 times).

After correctly programming the selected address, one additional program pulse with pulse width 3 times that needed for programming is applied.

When programming has been completed, the data in all addresses should be verified with $V_{CC}=V_{PP}=5V$.

The High Speed Program II Algorithm (shown in figure 2, page I-5) may also be used to reduce the programming time further.

ELECTRIC SIGNATURE MODE

Electric signature mode allows to read out a code from TMM2464AP/AF which identifies its manufacturer and device type.

The programming equipment may read out manufacturer code and device code from TMM2464AP/AF by using this mode before program operation and automatically set program voltage (V_{PP}) and algorithm.

Electric signature mode is set up when 12V is applied to address line A9 and the rest of address lines is set to V_{IL} in read operation. Data output in this conditions is manufacturer code. Device code is identified when address A0 is set to V_{IH}. These two codes possess an odd parity with the parity bit of MSB (O7).

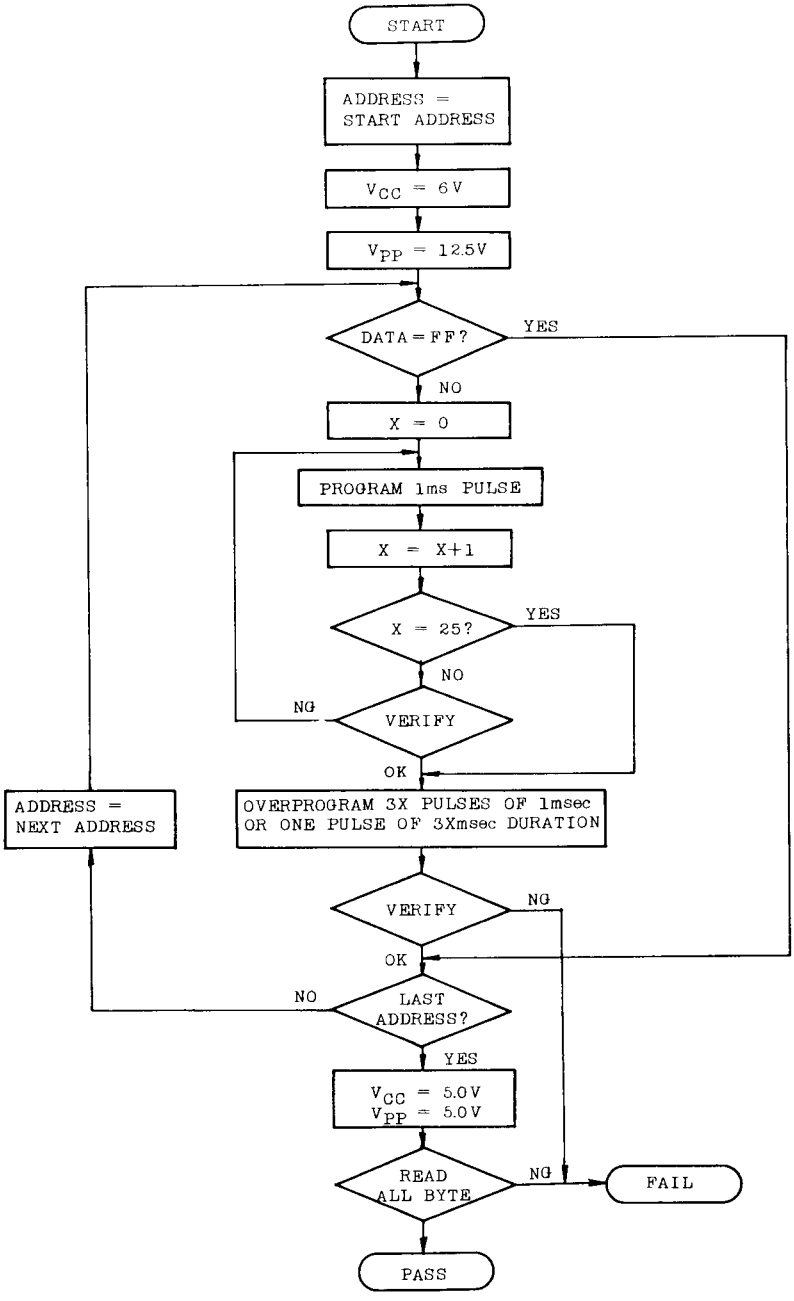
The following table shows electric signature of TMM2464AP/AF

PINS / SIGNATURE	A_0 (10)	O_7 (19)	O_6 (18)	O_5 (17)	O_4 (16)	O_3 (15)	O_2 (13)	O_1 (12)	O_0 (11)	HEX DATA
Manufacture Code	V_{IL}	1	0	0	1	1	0	0	0	98
Device Code	V_{IH}	0	1	0	1	0	0	1	0	52

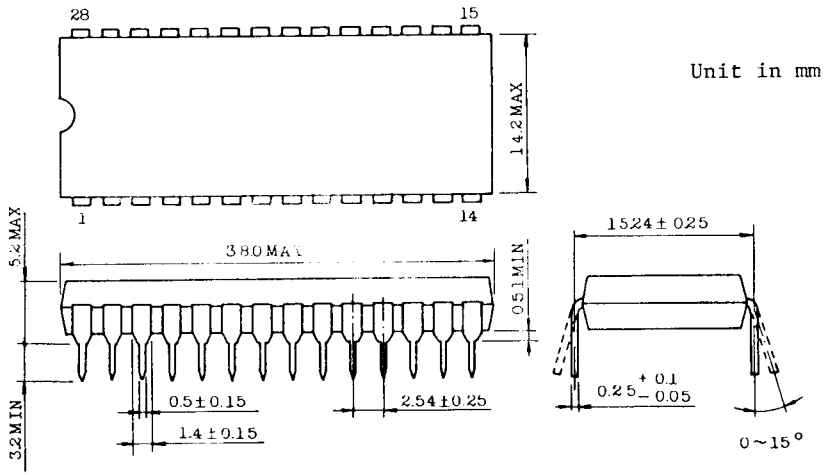
Notes: A9 = 12V±0.5V

A1~A8, A10~A12, $\overline{CE}$, $\overline{OE}=V_{IL}$ $\overline{PGM}=V_{IH}$

HIGH SPEED PROGRAM MODE FLOW CHART

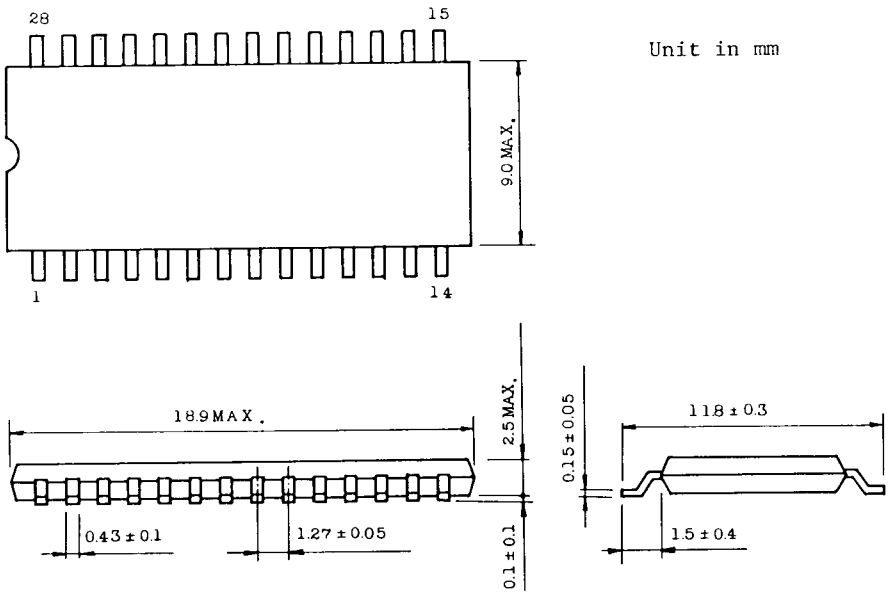


OUTLINE DRAWINGS (TMM2464AP)



Note : 1. Each lead pitch is 2.54mm. All leads are located within 0.25mm of their true longitudinal positson with respect No.1 and No.28 leads.
2. This value is measured at the end of leads.
3. All dimensions are in millimeters.

OUTLINE DRAWINGS (TMM2464AF)



Note : Lead pitch is 1.27 and tolerance is ±0.12 against theoretical center of each lead that is obtained on the basis of No.1 and No.28 leads.